

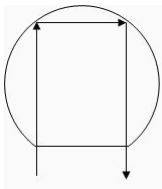
Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0 Diameter	150.00 +/- 0.50 mm	Wafer Vendor
	2.0 Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0 Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0 Secondary Flat Orientation	none	
	5.0 Edge Rounding	Semi M1	Wafer Vendor
	6.0 Overall Thickness	511.00 +/- 6.00 µm	ADE, 100%
	7.0 Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	8.0 Global Flatness (TIR)	<3.00µm	ADEmeasurement 100%
	9.0 Bow	<100.00µm	ADE to ASTM F534, 20%
	10.0 Warp	<100.00µm	ADE to ASTM F657, 20%
	11.0 Edge Chips	0	Bright Light, 100% (note 2)
	12.0 Edge Exclusion	5mm	
HandleSilicon	13.0 Handle Growth Method	CZ	Wafer Vendor
	14.0 Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	15.0 Handle Doping Type	Any	Wafer Vendor
	16.0 Handle Dopant	Any	Wafer Vendor
	17.0 Handle Resistivity	>1 Ohmcm	Wafer Vendor
	18.0 Handle Thickness	500.00 +/- 5.00 um	ADE, 100%inspection
	19.0 Backside Finish	Lapped with oxide and laserwith mask	Guaranteed by Process
BuriedOxide	24.0 Oxide Type	Thermal	Guaranteed by process
	25.0 Oxide formed on	Device and handle wafers	Guaranteed by process
	26.0 Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
DeviceSilicon	33.0 Device Growth Method	CZ	Wafer Vendor
	34.0 Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	35.0 Device Doping Type	N	Wafer Vendor
	36.0 Device Dopant	Phosphorous	Wafer Vendor
	37.0 Device Resistivity	1 - 3 Ohmcm	Wafer Vendor
	38.0 Nominal Thickness	9.50 +/- 0.75 um	FTIR or Filmetrics 9 point measurement
	39.0 Distance to device silicon edge from wafer edge	<2mm	Guaranteed by process
	40.0 Surface	roughness < 3A rms	Guaranteed by process
	41.0 Voids	none inside 5mm edge exclusion	Bright Light inspection 100%
	42.0 Scratches	none	Bright Light inspection 100%
	43.0 Haze	none	Bright Light inspection
	44.0 Device Field Oxidation	5,000.00 +/- 250.00 A	Nanospec centre point, 4%

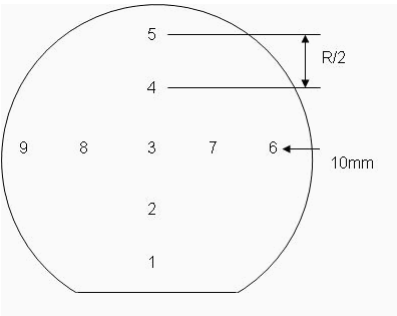
Part Number	Customer
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information